

CMOSH2-4L
SURFACE MOUNT
HIGH CURRENT, LOW V_F
SILICON SCHOTTKY DIODE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMOSH2-4L is a high current, low V_F silicon Schottky diode in an SOD-523 surface mount package. This device offers a V_F as low as 0.33 volts and is designed for small signal general purpose applications where size and low loss is required.

MARKING CODE: 4L

ULTRAmiTM



SOD-523 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Continuous Forward Current	I_F	200	mA
Peak Repetitive Forward Current	I_{FRM}	350	mA
Peak Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	1.0	A
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	500	$^\circ\text{C/W}$

SYMBOL

V_{RRM}	40	V
I_F	200	mA
I_{FRM}	350	mA
I_{FSM}	1.0	A
P_D	250	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	500	$^\circ\text{C/W}$

UNITS

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

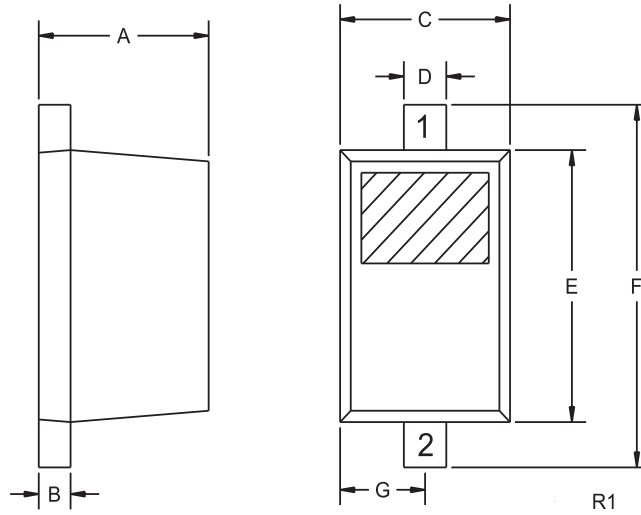
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=20\text{V}$		11	50	μA
BV_R	$I_R=100\mu\text{A}$	40	53		V
V_F	$I_F=10\text{mA}$		0.24	0.325	V
V_F	$I_F=100\text{mA}$		0.35	0.4	V
V_F	$I_F=200\text{mA}$		0.42	0.5	V
C_T	$V_R=4.0\text{V}, f=1.0\text{MHz}$		8.5	10	pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$		4.0	5.0	ns

R3 (25-January 2010)

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SOD-523 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: 4L

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.004	0.008	0.10	0.20
C	0.028	0.035	0.70	0.90
D	0.008	0.011	0.20	0.28
E	0.039	0.055	1.00	1.40
F	0.055	0.071	1.40	1.80
G	0.016		0.40	

SOD-523 (REV: R1)

R3 (25-January 2010)

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